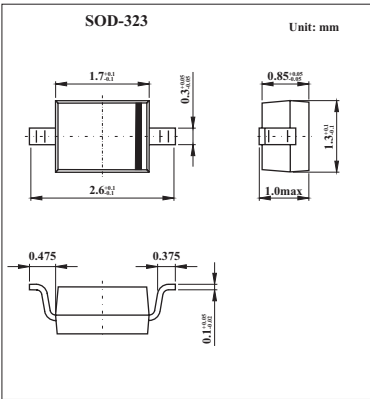


Silicon Epitaxial Planar Diode

1SV277

■ Features

- High Capacitance Ratio: $C_{1V}/C_{4V} = 2.30\text{Typ.}$
- Low Series Resistance: $r_s = 0.42\ \Omega$ (Typ.)



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	10	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1\ \mu\text{A}$	10			V
Reverse Current	I_R	$V_R = 10\ \text{V}$			3	nA
Capacitance	C_{1V}	$f = 1\ \text{MHz}; V_R = 1\ \text{V}$	4	4.5	4.9	pF
	C_{4V}	$f = 1\ \text{MHz}; V_R = 4\ \text{V}$	1.85	2	2.35	
Capacitance Ratio	C_{1V}/C_{4V}		2	2.3		
Series Resistance	r_s	$V_R = 1\ \text{V}, f = 470\ \text{MHz}$		0.42	0.55	Ω

■ Marking

Marking	TO
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